



MSC1035M

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI MSC1035M** is Designed for Class C, DME/TACAN Applications up to 1150 MHz.

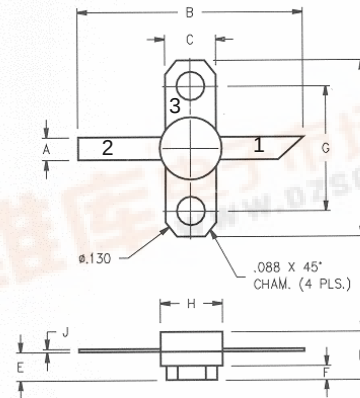
FEATURES:

- Class C Operation
- $P_G = 10.7$ dB at 35 W/1150 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	3.0 A PEAK
V_{CB}	65 V
P_{DISS}	150 W PEAK
T_J	-65 °C to +250 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	1.0 °C/W

PACKAGE STYLE .280 2L FLG



	MINIMUM INCHES/MM	MAXIMUM INCHES/MM		MINIMUM INCHES/MM	MAXIMUM INCHES/MM
A	.100/2,54		J	.003/0,08	.006/0,15
B	1.050/26,67				
C	.250/6,35				
D		.210/5,33			
E	.120/3,05	.130/3,30			
F	.062/1,58				
G	.562/14,28				
H		.285/7,24			
I	.800/20,32				

1 = Collector 2 = Emitter 3 = Base

CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 10$ mA	65			V
BV_{CER}	$I_C = 10$ mA $R_{BE} = 10$ Ω	65			V
BV_{EBO}	$I_E = 1.0$ mA	3.5			V
I_{CES}	$V_{CB} = 50$ V			5.0	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 500$ mA	15		120	---
P_G	$V_{CC} = 50$ V $P_{OUT} = 35$ W $f = 1025 - 1150$ MHz	10.7	11.2		dB
η_c	$P_{IN} = 3.0$ W	43	48		%

Pulse width = 10 μ Sec, Duty Cycle = 1 %

